

## isc Silicon NPN Power Transistor

## BDS12

## DESCRIPTION

- High Voltage:  $V_{CEV} = 100V(\text{Min})$
- Low Saturation Voltage-  
:  $V_{CE(\text{sat})} = 1.0V(\text{Max}) @ I_C = 5A$
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

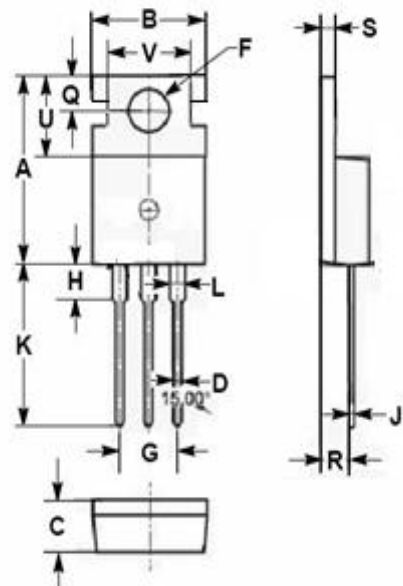
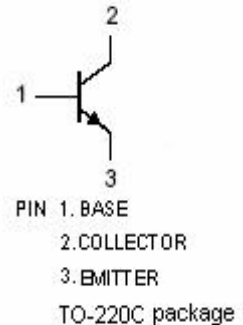
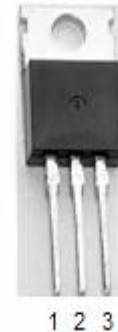
- Designed for power linear and switching application and General puepose power.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEV}$	Collector-Emitter Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	15	A
$I_B$	Base Current	5	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	90	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.4	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	80	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

**isc Silicon NPN Power Transistor****BDS12****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=50\text{mA}; I_B=0$	100			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=2.5\text{A}$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=2.5\text{A}$			2.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CE}=100\text{V}; V_{BE}=0$			0.5	mA
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=50\text{V}; V_{BE}=0$			1.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1.0	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=4\text{V}$	40		250	
$h_{FE-2}$	DC Current Gain	$I_C=5\text{A}; V_{CE}=4\text{V}$	15		150	
$h_{FE-3}$	DC Current Gain	$I_C=10\text{A}; V_{CE}=4\text{V}$	5			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=4\text{V}$	3			MHz

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